



GAU: 3905 #4/IDS
2814 8/8/00
Short

DOCKET NO.: 3905

#4/IDS
8/8/00
Short

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN THE MATTER OF THE APPLICATION FOR PATENT

OF: Takao NAKAMURA et al.

Art Unit: 2811

SERIAL NO.: 09/519,408

FILED: March 3, 2000

FOR: SEMICONDUCTOR LIGHT-EMITTING DEVICE, METHOD
OF MANUFACTURING TRANSPARENT CONDUCTOR FILM
AND METHOD OF MANUFACTURING COMPOUND SEMI-
CONDUCTOR LIGHT-EMITTING DEVICE

RECEIVED

AUG 07 2000

TECHNOLOGY CENTER 2800

COMMISSIONER FOR PATENTS

July 31, 2000

WASHINGTON, D. C. 20231

INFORMATION DISCLOSURE STATEMENT AND CERTIFICATE OF MAILING

Dear Sir:

- 1) Pursuant to 37 C.F.R. §§ 1.56, 1.97 and 1.98 applicant encloses a second Form PTO-1449 and copies of the references listed thereon. Applicant is also enclosing a copy of an English translation of a Japanese Office Action issued on May 16, 2000 in a corresponding Japanese Patent application. Applicant requests that the references be made of record.
- 2) This statement is being filed before the mailing date of a first Office Action on the merits, to the best knowledge of the undersigned.
- 3) The undersigned hereby certifies that each item of information contained in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement, as seen from the Japanese Office Action date of May 16, 2000.

4) Reference AB is accompanied by an English language Abstract and reference AC is accompanied by a partial English Translation. Furthermore, the references are being cited herein because the Japanese Examiner found them to be relevant to the corresponding Japanese application. The Japanese Examiner's assertions as set forth in the enclosed translation of the Japanese Office Action are not agreed to or ratified by the applicant, but are merely submitted as a reason why the references are being cited herein.

5) Applicant respectfully requests that the Examiner consider all references of record, return an initialled copy of the enclosed second Form PTO-1449 and ensure that all references of record are printed on any patent issuing from this application.

6) Favorable consideration and allowance of claims 1 to 15 are respectfully requested.

Respectfully submitted

Takao NAKAMURA et al.
Applicant

By 
Walter F. Fasse
Patent Attorney
Reg. No.: 36132
Tel. No.: 207-938-4422
Fax. No.: 207 938 2323
P. O. Box K
St. Albans, ME 04971

WFF:ar/3905
Enclosure: postcard,
Form PTO-1449,
2 references, English
Translation of Japanese
Office Action

CERTIFICATE OF MAILING:

I hereby certify that the foregoing Information Disclosure Statement with enclosures is being mailed on July 31, 2000 as first class mail, postage pre-paid, in an envelope addressed to: Commissioner for Patents, Washington, D. C. 20231.

Margit Ettinger 7/31/00
Margit Ettinger - July 31, 2000



Docket# 3905
USSN:09/519,408
A-U:2811

Mailed May 16, 2000

NOTICE OF GROUND OF REJECTION

RECEIVED

AUG 07 2000

TECHNOLOGY CENTER 2800

Patent Application No. 11-107586
Patent Office Examiner: Masahiro TAKAKI
To Attorney, Mr. Hisao FUKAMI (et al.):

The present application shall be recognized to be rejected on the ground as described below. It is required that the remarks, if any, be submitted within sixty days of the date on which the present NOTICE was mailed.

G R O U N D

It is recognized that, because the invention described in Claim(s) of SCOPE OF CLAIMS FOR PATENT of the present application could have been invented readily by a person having ordinary knowledge in the field of the art to which the present invention pertains prior to the filing of the present application based on the invention as described in the following publication(s) distributed in Japan and/or foreign countries prior to the filing of the present application, a patent cannot be granted thereto under the provision of Paragraph 2 of Article 29 of the Patent Law.

Remarks (as to cited references,
see appended List of Cited References)

- Claim 1-8
- References 1, 2
- Note

As disclosed in reference 1, it is known that a target is irradiated with a laser beam and thus abraded to discharge atoms or molecular ions to deposit them on a substrate and as the atoms or molecular ions are oxidized they are grown to be a crystal to provide a transparent conductive film.

Furthermore, the target may be of any material depending on the transparent conductive film to be provided that would be determined by those skilled in the art, as appropriate, and it is known that In_2O_3 -10wt% ZnO is used to form a transparent conductive film, as disclosed in Japanese Patent Laying-Open No. 6-318406.

Furthermore, it is well known that transparent

conductive film is used to form a transparent electrode of a compound semiconductor light-emitting device. As such, applying the method of preparing a transparent conductive film, as disclosed in Japanese Patent Laying-Open No. 9-59762, to a method of fabricating a transparent electrode of a compound semiconductor light-emitting device, is not inventive.

List of Cited References

1. Japanese Patent Laying-Open No. 9-59762
2. Japanese Patent Laying-Open No. 6-318406

RECORD OF SEARCH FOR PRIOR ART DOCUMENTS

• SEARCHED TECHNICAL FIELD
IPC SEVENTH EDITION H01B13/00, H01L33/00
C23C14/00-14/58
DB NAME JICST file

• PRIOR ART DOCUMENTS
Japanese Patent Laying-Open No. 2000-44236

The record of prior art search results does not constitute a Ground of Rejection.